



Corrigendum

Corrigendum to “Interface formation between CuIn_{1-x}GaxSe₂ absorber and In₂S₃ buffer layer deposited by ultrasonic spray pyrolysis”
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The authors regret that during the publication of this paper the following errors occurred. The authors would like to apologise for any inconvenience this may have caused.

In the whole article (abstract included) the terms [Ga]/([Ga] ± [In]) and [Cu]/([Ga] ± [In]) are incorrect. They should read [Ga]/([Ga] + [In]) and [Cu]/([Ga] + [In]).

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